

FIG. 1

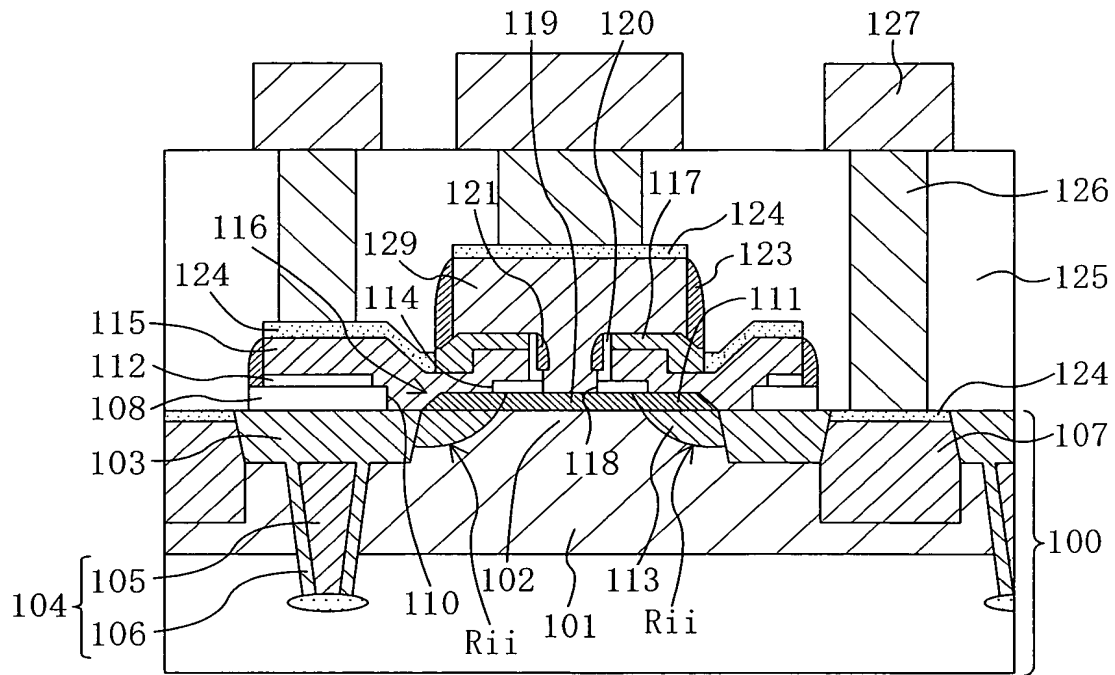


FIG. 2(a)

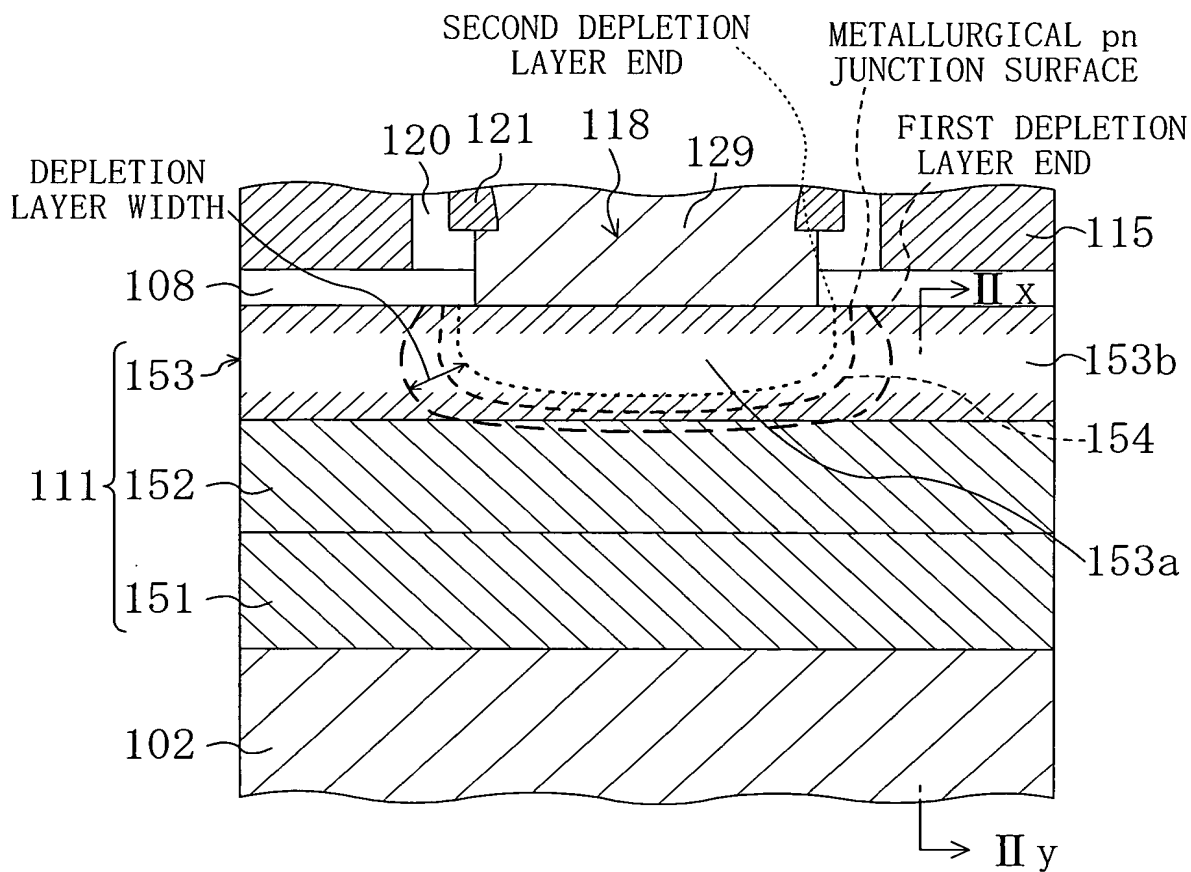
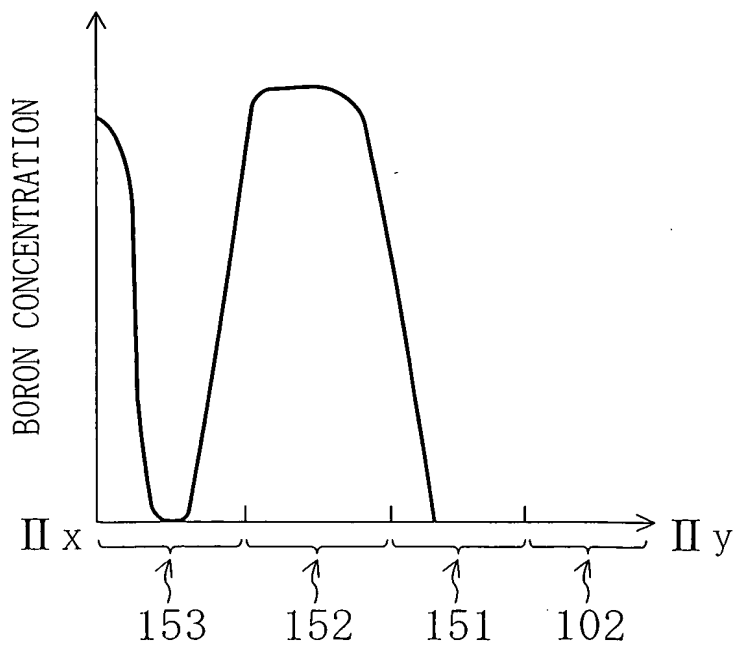


FIG. 2(b)



A cross-sectional view of a semiconductor device 100. The device includes a substrate 101 with a patterned layer 102. A top layer 103 is formed on the substrate. A central structure 104 is formed by a layer 105 and a base 106. The structure is surrounded by a material 107.

[illegible]

FIG. 5(a)

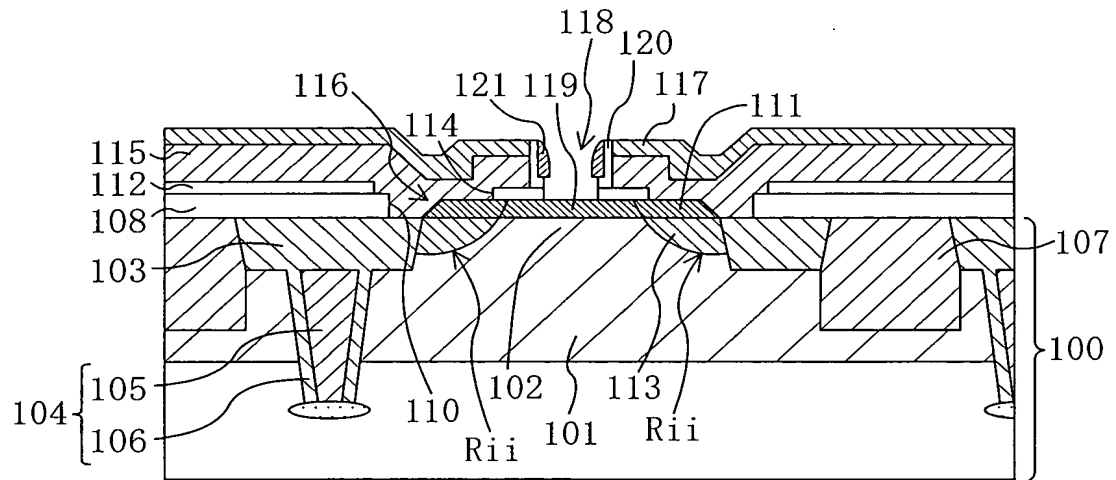
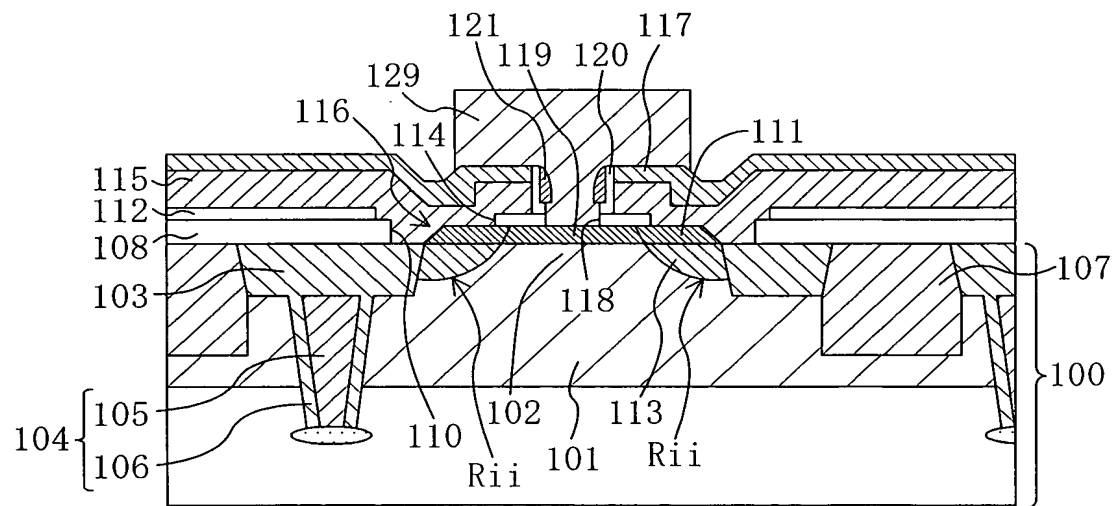


FIG. 5(b)



[illegible]

FIG. 7(a)

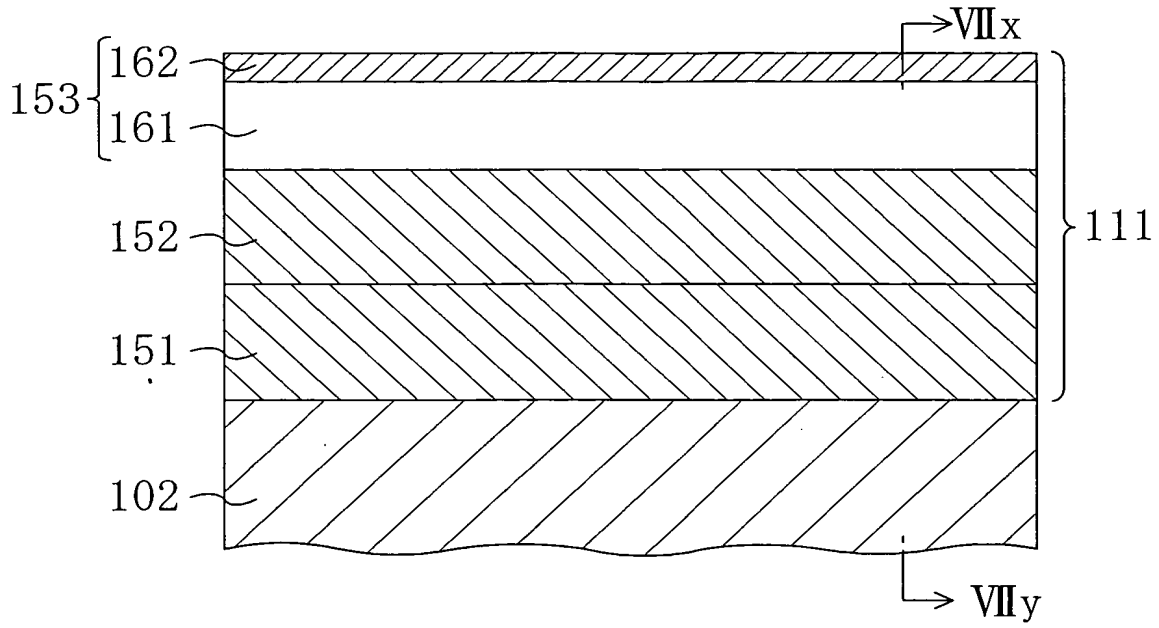


FIG. 7(b)

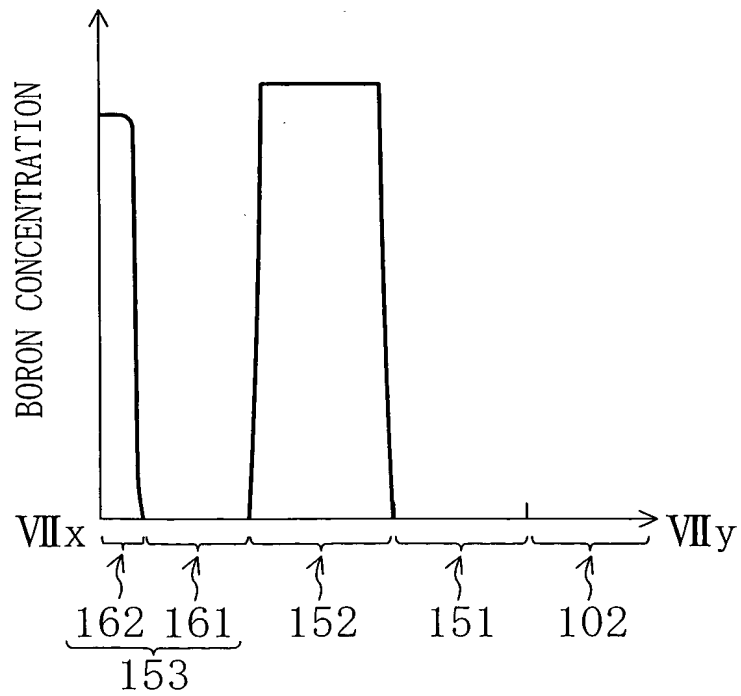


FIG. 8(a)

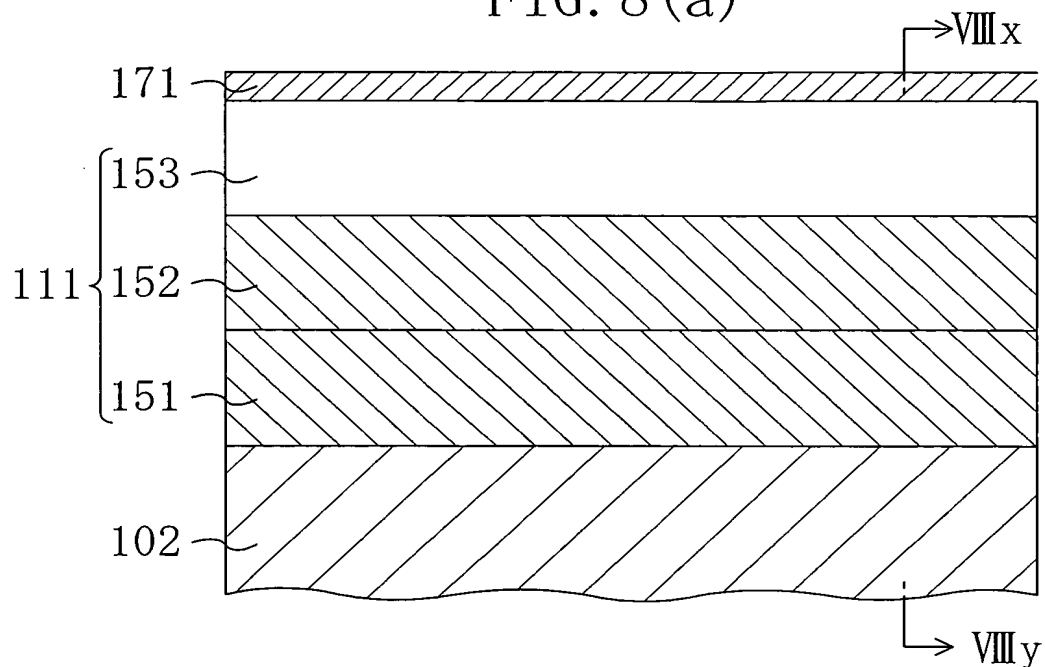


FIG. 8(b)

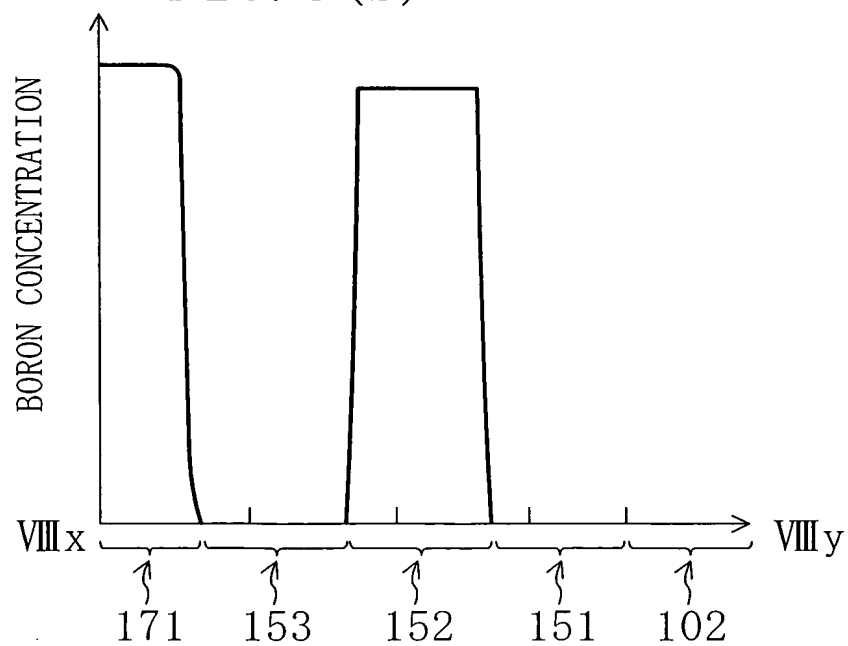




FIG. 9(a)

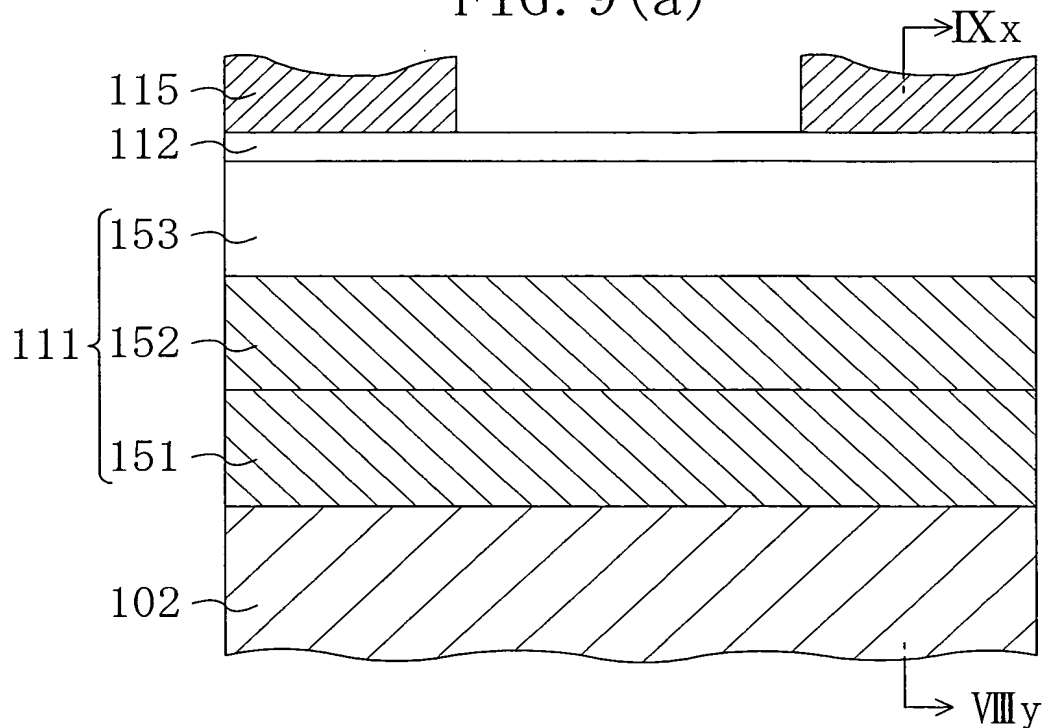


FIG. 9(b)

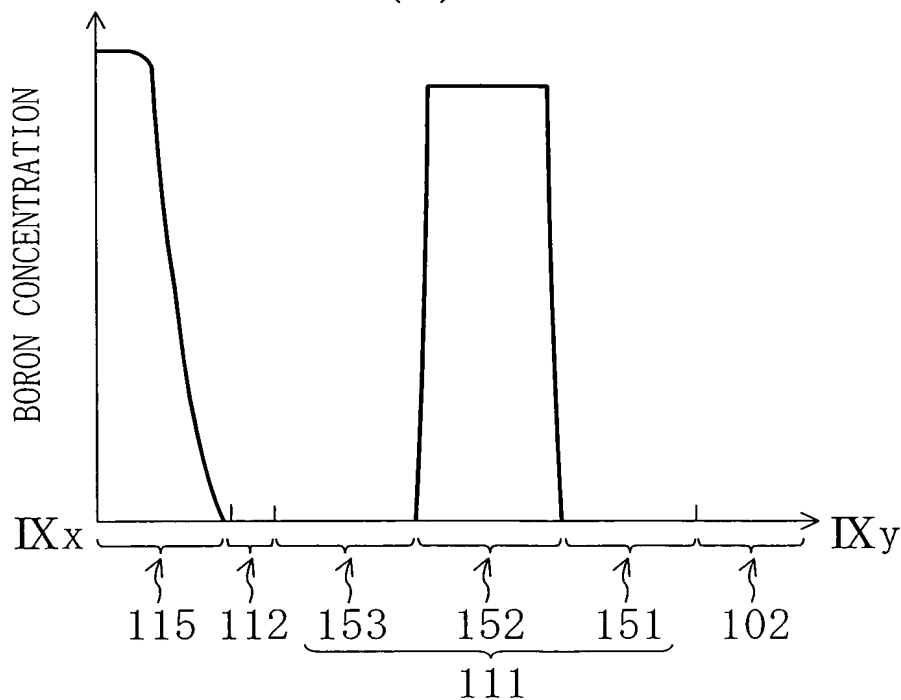
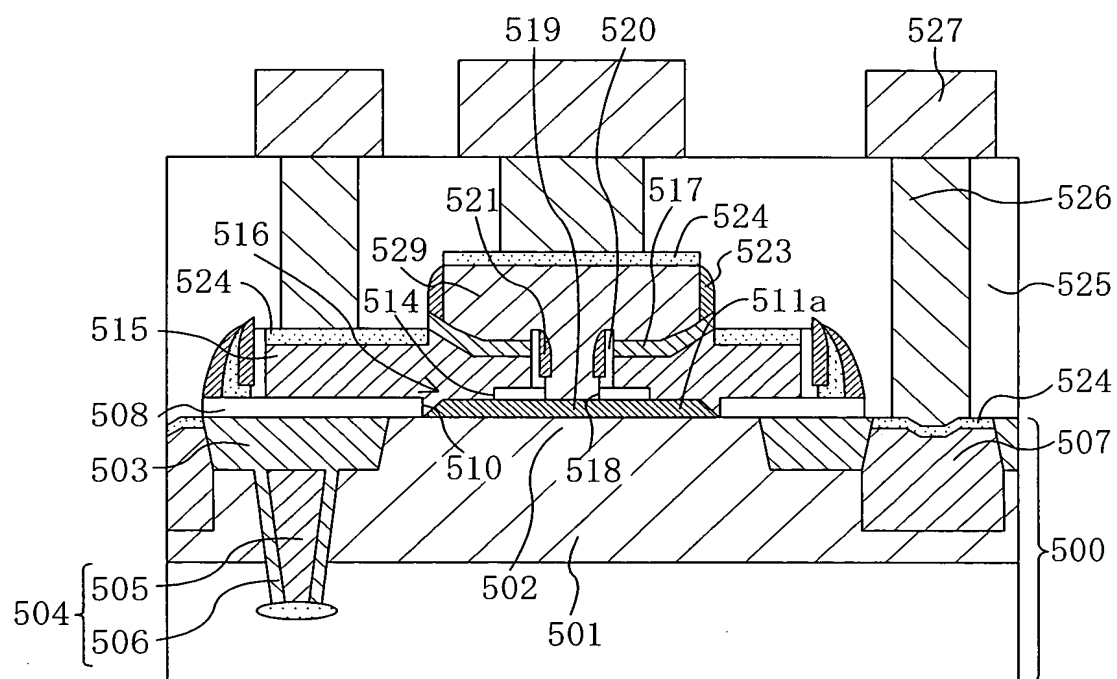
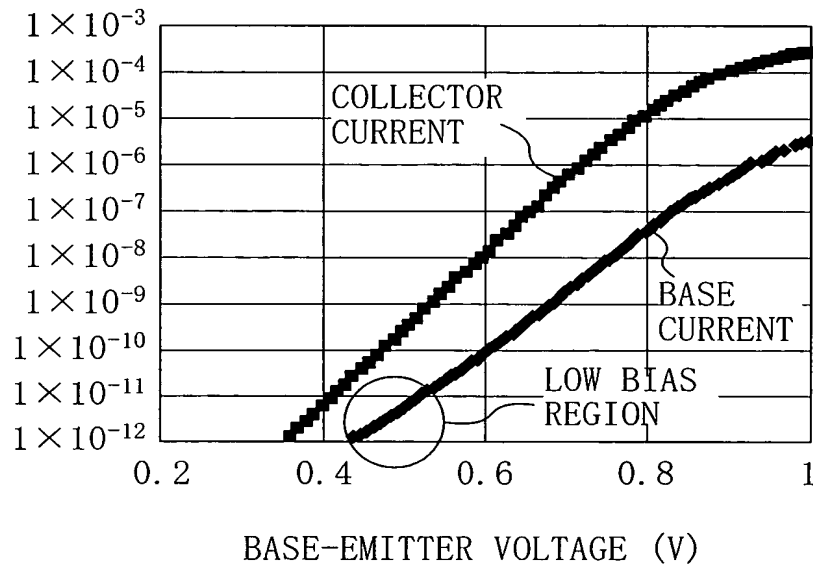


FIG. 10



BASE CURRENT, COLLECTOR CURRENT (A)

FIG. 11 (a)



BASE CURRENT, COLLECTOR CURRENT (A)

FIG. 11 (b)

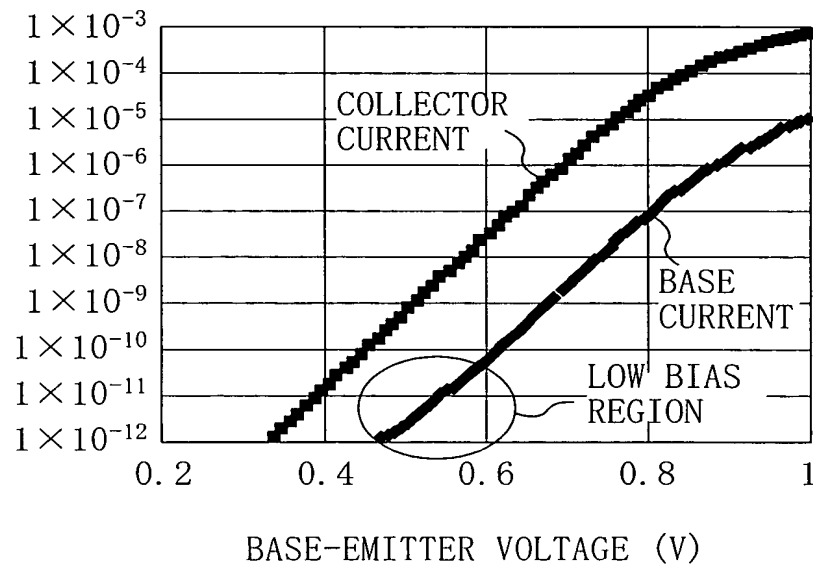


FIG. 12(a)

PRIOR ART

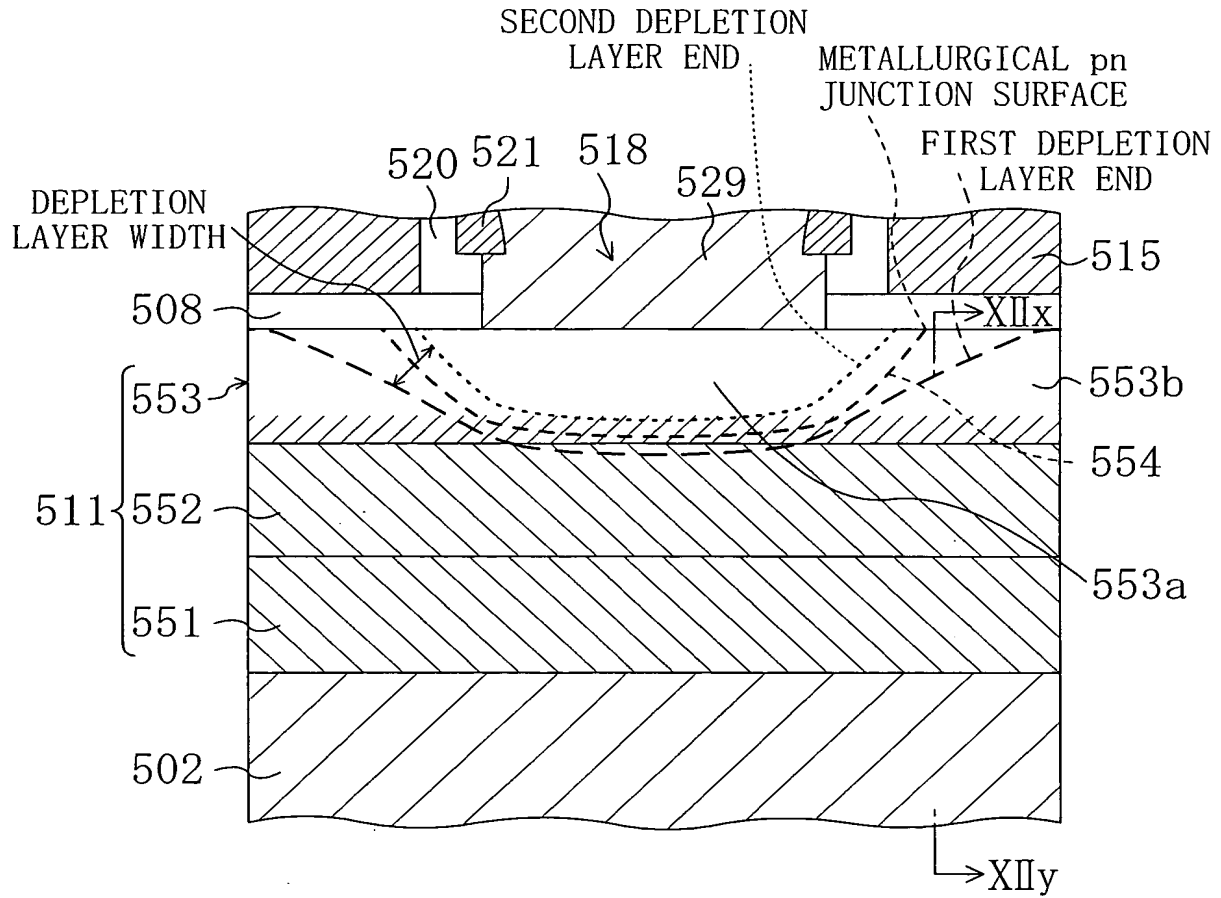


FIG. 12(b)

PRIOR ART

